sidewalls and said core that causes electron transfer when said sensing sidewalls are struck with light.

- (Original) The method in claim 20, wherein said logic circuitry blocks light from said core.
- 24. (Original) The method in claim 20, wherein said forming of said trenches forms four vertical sidewalls around said core.
- 25. (Original) The method in claim 20, further comprising doping said core with impurities to form an n+ core and doping said sidewalls with impurities to form p+ sidewalls.
- 26. (Original) A method of forming an array of island photodiodes comprising: forming cores in a substrate; forming trenches in sald substrate adjacent said cores; forming light sensing sidewalls along said trenches; and forming logic circuitry above each of said cores.
- 27. (Original) The method in claim 26, wherein said sidewalls are perpendicular to a surface of said photodiode that receives incident light.
- 28. (Original) The method in claim 26, wherein said forming of said light sensing sidewalls comprises doping sidewalls of said trench to form a junction region between said sidewalls and said cores that causes electron transfer when said sensing sidewalls are struck with light.

- 29. (Original) The method in claim 26, wherein said logic circuitry blocks light from said cores.
- 30. (Original) The method in claim 26, wherein said forming of said trenches forms four vertical sidewalls around each of said cores.
- 31. (Original) The method in claim 26, further comprising doping said cores with impurities to form an n+ core and doping said sidewalls with impurities to form p+ sidewalls.

32-33 (Cancelled).

Respectfully submitted,

Frederick W. Gibb, III Registration No.: 37,629

Date: 1/4/04 McGinn & Gibb, PLLC. 2568-A Riva Road, Suite 304 Annapolis, Maryland 21401 (301) 261-8071 Customer No. 29154